

MOS INTEGRATED CIRCUIT μ PD4416008

16M-BIT CMOS FAST SRAM 2M-WORD BY 8-BIT

Description

The μ PD4416008 is a high speed, low power, 16,777,216 bits (2,097,152 words by 8 bits) CMOS static RAM. Operating supply voltage is 3.3 V \pm 0.3 V.

The μ PD4416008 is packaged in a 54-PIN PLASTIC TSOP (II) (10.16 mm (400))

Features

• 2,097,152 words by 8 bits

• Fast access time: 15, 17 ns (MAX.)

• Output Enable input for easy application

Ordering Information

Part number	Package	Supply voltage	Access time	Supply currer	nt mA (MAX.)
		V	ns (MAX.)	At operating	At standby
μPD4416008G5-A15-9JF	54-PIN PLASTIC TSOP (II)	3.3 ± 0.3	15	230	10
μPD4416008G5-A17-9JF	(10.16 mm (400))		17	220	

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



Pin Configuration (Marking Side)

/xxx indicates active low signal.

54-PIN PLASTIC TSOP (II) (10.16 mm (400)) $[\mu \text{PD4416008G5-xxx-9JF}]$

			1
NC O	1	54	NC
Vcc O	2	53	——O GND
NC O	3	52	——O NC
1/0 7 ○ ← →	4	51	1/0 6
GND O-	5	50	Vcc Vcc
I/O 8 ○ < →	6	49	- I/O 5
A0 ○ →	7	48	A20
A1 ○ →	8	47	→ A19
A2 ○ →	9	46	→ O A18
A3 ○	10	45	← ○ A17
A4 ○ →	11	44	→ ○ A16
NC O	12	43	NC
/CS ○	13	42	
Vcc O	14	41	— GND
/WE ○	15	40	ic
NC O	16	39	← ○ A15
A5 ○	17	38	← ○ A14
A6 ○	18	37	← ○ A13
A7 ○	19	36	← ○ A12
A8 ○ 	20	35	<○ A11
A9 ○ 	21	34	→ ○ A10
I/O 1 ○ < →	22	33	→ ○ I/O 4
Vcc O	23	32	——— GND
I/O 2 ○ < →	24	31	 ○ I/O 3
NC O	25	30	——○ NC
GND ○	26	29	——○ Vcc
NC O-	27	28	——○ NC
]

A0 - A20 : Address Inputs

I/O1 - I/O8 : Data Inputs / Outputs

/CS : Chip Select
/WE : Write Enable
/OE : Output Enable
Vcc : Power supply

GND : Ground

NC : No connection

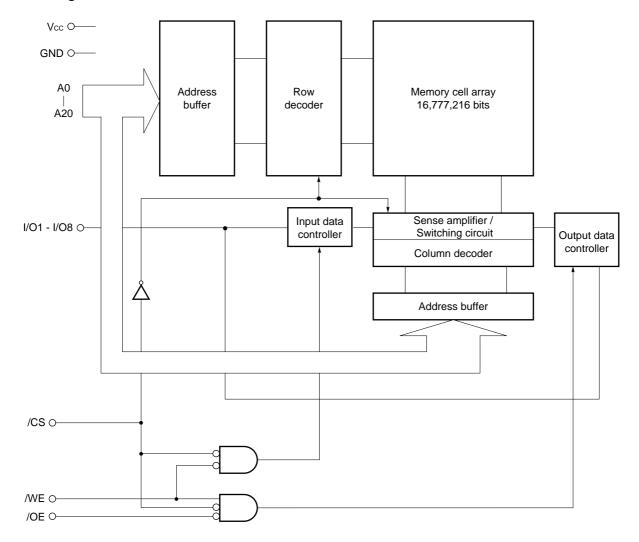
IC : Internal connection Note

Note Leave this pin connect to GND.

Remark Refer to **Package Drawing** for 1-pin index mark.



Block Diagram



Truth Table

/CS	/OE	/WE	Mode	I/O	Supply current
Н	×	×	Not selected	High impedance	Isв
L	L	Н	Read	D оит	Icc
L	×	L	Write	Din	
L	Н	Н	Output disable	High impedance	

Remark ×: Don't care

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Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	Vcc		-0.5 ^{Note} to +4.0	V
Input / Output voltage	VT		-0.5 ^{Note} to +4.0	٧
Operating ambient temperature	TA		0 to 70	°C
Storage temperature	Tstg		-55 to +125	°C

Note -2.0 V (MIN.) (pulse width: 2 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	Vcc		3.0	3.3	3.6	V
High level input voltage	VIH		2.0		Vcc + 0.3	V
Low level input voltage	VIL		-0.3 Note		+0.8	V
Operating ambient temperature	TA		0		70	°C

Note -2.0 V (MIN.) (pulse width: 2 ns)

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

Parameter	Symbol	Test condit	MIN.	TYP.	MAX.	Unit	
Input leakage current	lu	Vin = 0 V to Vcc		-2		+2	μΑ
Output leakage current	ILO	$V_{I/O} = 0 \text{ V to Vcc, /CS} = V_{IH}$ $/WE = V_{IL}$	-2		+2	μΑ	
Operating supply current	Icc	/CS = VIL, II/O = 0 mA,	Cycle time : 15 ns			230	mA
		Minimum cycle time	Cycle time : 17 ns			220	
Standby supply current	Isв	/CS = VIH, VIN = VIH OF VIL,	/CS = VIH, VIN = VIH or VIL, Minimum cycle time			80	mA
	I _{SB1}	/CS ≥ Vcc - 0.2 V,	/CS ≥ Vcc – 0.2 V,			10	
		$V_{\text{IN}} \le 0.2 \text{ V or } V_{\text{IN}} \ge V_{\text{CC}} - 0$					
High level output voltage	Vон	Iон = −4.0 mA	2.4			V	
Low level output voltage	Vol	loL = +8.0 mA				0.4	V

 $\textbf{Remark} \quad V_{\text{IN}}: Input \ voltage, \ V_{\text{I/O}}: Input \ / \ Output \ voltage$

Capacitance (TA = 25 °C, f = 1 MHz)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	V _{IN} = 0 V			6	pF
Input / Output capacitance	C _{I/O}	V _V O = 0 V			8	pF

Remarks 1. VIN: Input voltage, VI/O: Input / Output voltage

2. These parameters are periodically sampled and not 100% tested.

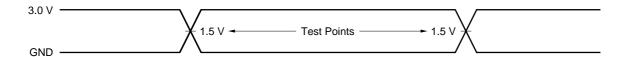


AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

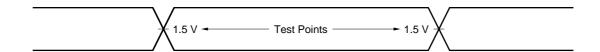
AC Test Conditions

LVTTL Interface

Input Waveform (Rise and Fall Time ≤ 3 ns)

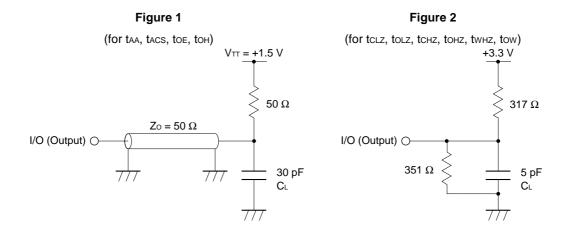


Output Waveform



Output Load

AC characteristics directed with the note should be measured with the output load shown in Figure 1 or Figure 2.



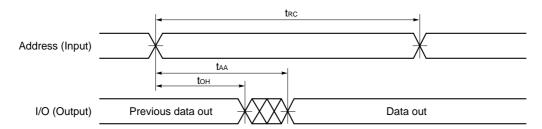
Remark C_L includes capacitances of the probe and jig, and stray capacitances.

Read Cycle

Parameter	Symbol	-A 15		-A17		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Read cycle time	trc	15		17		ns	
Address access time	t AA		15		17	ns	1
/CS access time	tacs		15		17	ns	
/OE access time	toe		7		8	ns	
Output hold from address change	tон	3		3		ns	
/CS to output in low impedance	tcız	3		3		ns	2, 3
/OE to output in low impedance	toLZ	0		0		ns	
/CS to output in high impedance	tснz		7		8	ns	
/OE to output hold in high impedance	tонz		7		8	ns	

- Notes 1. See the output load shown in Figure 1.
 - 2. Transition is measured at ± 200 mV from steady-state voltage with the output load shown in **Figure 2**.
 - 3. These parameters are periodically sampled and not 100% tested.

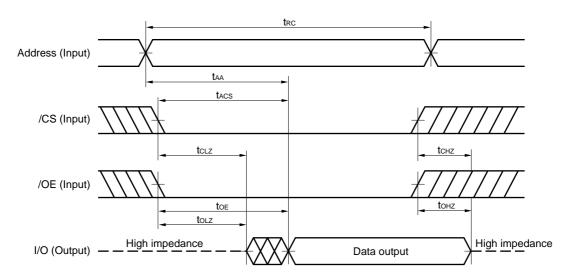
Read Cycle Timing Chart 1 (Address Access)



Remarks 1. In read cycle, /WE should be fixed to high level.

2. /CS = /OE = VIL

Read Cycle Timing Chart 2 (/CS Access)



Caution Address valid prior to or coincident with /CS low level input.

Remark In read cycle, /WE should be fixed to high level.



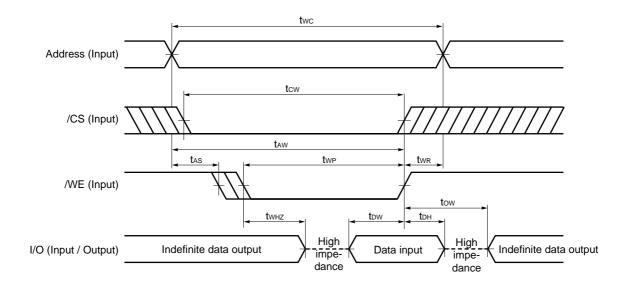
Write Cycle

Parameter	Symbol	-A15		-A17		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	15		17		ns	
/CS to end of write	tcw	10		11		ns	
Address valid to end of write	taw	10		11		ns	
Write pulse width	t wp	10		11		ns	
Data valid to end of write	tow	7		8		ns	
Data hold time	t DH	0		0		ns	
Address setup time	t as	0		0		ns	
Write recovery time	twr	1		1		ns	
/WE to output in high impedance	twнz		7		8	ns	1, 2
Output active from end of write	tow	3		3		ns	

Notes 1. Transition is measured at \pm 200 mV from steady-state voltage with the output load shown in **Figure 2**.

2. These parameters are periodically sampled and not 100% tested.

Write Cycle Timing Chart 1 (/WE Controlled)



Cautions 1. /CS or /WE should be fixed to high level during address transition.

2. Do not input data to the I/O pins while they are in the output state.

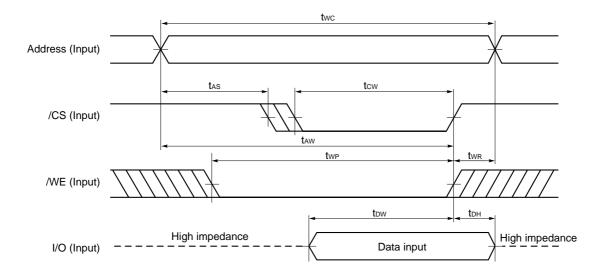
Remarks 1. Write operation is done during the overlap time of a low level /CS, a low level /WE.

- 2. During twHz, I/O pins are in the output state, therefore the input signals of opposite phase to the output must not be applied.
- 3. When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.

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Write Cycle Timing Chart 2 (/CS Controlled)



Cautions 1. /CS or /WE should be fixed to high level during address transition.

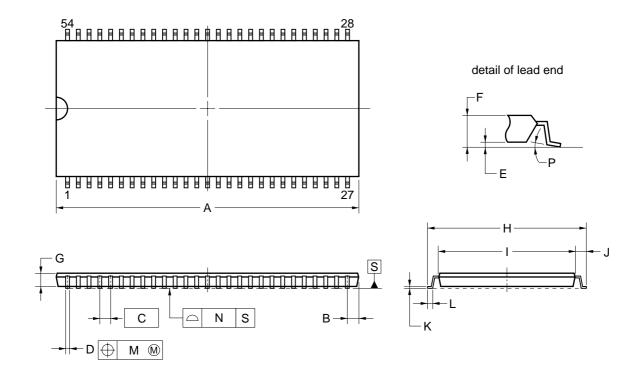
2. Do not input data to the I/O pins while they are in the output state.

Remark Write operation is done during the overlap time of a low level /CS and a low level /WE.



Package Drawing

54-PIN PLASTIC TSOP (II) (10.16 mm (400))



NOTES

- 1. Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.
- Dimension "A" does not include mold fiash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per side.

ITEM	MILLIMETERS
A	22.22±0.05
В	0.91 MAX.
С	0.80 (T.P.)
D	$0.32^{+0.08}_{-0.07}$
E	0.10±0.05
F	1.1±0.1
G	1.00
Н	11.76±0.20
- 1	10.16±0.10
J	0.80±0.20
K	$0.145^{+0.025}_{-0.015}$
L	0.50±0.10
М	0.13
N	0.10
Р	3°+7°

S54G5-80-9JF-2

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD4416008.

Type of Surface Mount Device

 $\mu\text{PD4416008}$: 54-PIN PLASTIC TSOP (II) (10.16 mm (400))



NOTES FOR CMOS DEVICES

(1) PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

3 STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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